

REPLACEMENT DISCLOSURE

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The present invention also uses existing silicon etching technology that offers high precision in both etch depth and gasket width when carving out the desired shape. This allows greater control over the dimensions of the hermetically sealed cavity. Also, due to the high strength of silicon, the gaskets can be made narrower than in the past – usually no more than 10 μm wide. The surface area of the gasket determines the amount of pressure on the bond juncture during bonding for a given bonding force. Since a narrower gasket has less surface area, it is able to concentrate more of the applied bonding force at the bond juncture to create a strong seal.

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In Figure 3C, the existing photoresist 303 is used as a mask to etch cap wafer 203. Selected portions of the cap wafer material are removed to create gasket 201. Any conventional etching process may be used, such as reactive ion etching (RIE) or deep reactive ion etching (DRIE). Gasket 201 is created from the same material as cap wafer 203. Usually, the material is silicon, which has good rigidity and hermeticity. In actual working embodiments, gasket 201 is between 3-12 μm wide and 4-10 μm deep. Other sizes for the gasket width and depth can be used to achieve the same purpose. Photoresist 303 is removed after gasket 201 is formed.